

HAOPIN MICROELECTRONICS CO.,LTD.

Description

Passivated, sensitive gate triacs in a plastic envelope, intended for use in general purpose bidirectional switching and phase control applications, where high sensitivity is required in all four quadrants.

Symbol	Simplified outline
	 TO-252
Pin	Description
1	Main terminal 1 (T1)
2	Main terminal 2 (T2)
3	gate (G)
TAB	Main terminal 2 (T2)

Applications:

- ◆ Motor control
- ◆ Industrial and domestic lighting
- ◆ Heating
- ◆ Static switching

Features

- ◆ Blocking voltage to 600 V
- ◆ On-state RMS current to 4 A

SYMBOL	PARAMETER	Value	Unit
V_{DRM}	Repetitive peak off-state voltages	600	V
$I_T \text{ (RMS)}$	RMS on-state current	4	A
I_{TSM}	Non-repetitive peak on-state current	40	A

SYMBOL	PARAMETER	MIN	TYP	MAX	UNIT
$R \theta_{jc}$	Thermal Resistance - Junction-to-case	-	-	3.5	°C/W
$R \theta_{ja}$	Thermal resistance - Junction to ambient	-	-	88	°C/W



MAC4DHM (G)

Sensitive Gate Triacs

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Limiting values in accordance with the Maximum system(IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V_{DRM}	Repetitive peak off-state Voltages	$T_j=-40$ to 110°C , sine wave, 50 to 60 Hz, Gate open	-	600	V
$I_{T(RMS)}$	RMS on-state current Full sine wave 60 Hz	$T_c=93^\circ\text{C}$	-	4	A
I^2t	Circuit fusing consideration	$t=8.3\text{ms}$	-	6.6	A^2s
I_{GM}	Peak gate current	Pulse width $\leq 10 \mu\text{s}$ $T_c=93^\circ\text{C}$	-	0.2	A
V_{GM}	Peak gate voltage	Pulse width $\leq 10 \mu\text{s}$ $T_c=93^\circ\text{C}$	-	5	V
P_{GM}	Peak gate power	Pulse width $\leq 10 \mu\text{s}$ $T_c=93^\circ\text{C}$	-	0.5	W
$P_{G(AV)}$	Average gate power	$t=8.3\text{ms}$ $T_c=108^\circ\text{C}$	-	0.1	W
T_{stg}	Storage temperature		-40	150	$^\circ\text{C}$
T_j	Operating junction Temperature range		-40	110	$^\circ\text{C}$

$T_j=25^\circ\text{C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
Static characteristics						
I_{GT}	Gate trigger current	$V_D=12\text{V}; R_L=100 \Omega$ MT2(+),G(+) MT2(+),G(-) MT2(-),G(-) MT2(-),G(+)	-	1.8 2.1 2.4 4.2	5 5 5 5	mA
V_{GT}	Gate trigger voltage	$V_D=12\text{V}; R_L=100 \Omega$ MT2(+),G(+) MT2(+),G(-) MT2(-),G(-) MT2(-),G(+)	0.5 0.5 0.5 0.5	0.62 0.57 0.65 0.74	1.3 1.3 1.3 1.3	V
I_L	Latching current	$V_D=12\text{V}, I_G=5.0 \text{ mA}$ $V_D=12\text{V}, I_G=5.0 \text{ mA}$ $V_D=12\text{V}, I_G=5.0 \text{ mA}$ $V_D=12\text{V}, I_G=10 \text{ mA}$ MT2(+),G(+) MT2(+),G(-) MT2(-),G(-) MT2(-),G(+)	- - - -	1.75 5.2 2.1 2.2	10 10 10 10	mA
I_{DRM} I_{RRM}	Peak Repetitive blocking current	$V_D=\text{Rated } V_{DRM}, V_{RRM};$ Gate open $T_j=25^\circ\text{C}$ $T_j=125^\circ\text{C}$	-	-	0.01 2.0	mA
I_H	Holding current	$V_D=12\text{V}$, gate open, Initiating current $= \pm 200\text{mA}$	-	1.5	15	mA
V_{TM}	Peak on-state voltage	$I_{TM}= \pm 6.0\text{A}$	-	1.3	1.6	V
V_{GD}	Gate Non-trigger voltage	$V_D=12\text{V}; R_L=100 \Omega$ $T_j=110^\circ\text{C}$	0.1	0.4	-	V

Dynamic Characteristics

D_V/dt	Critical rate of rise of Off-state voltage	$V_D=67\% V_{DRM}$ gate open; $T_j=110^\circ\text{C}$;	20	-	-	$\text{V}/\mu\text{s}$
$(dI/dt)c$	Rate of change of commutating current	$V_D=200\text{V}$, $I_{TM}=1.8\text{A}$ $dV/dt=1.0\text{V}/\mu\text{s}$ $T_j=110^\circ\text{C}$, $f=250\text{ Hz}$, $CL=5.0 \mu\text{F}$, $LL=80\text{ mH}$, $RS=56 \Omega$ $CS=0.03 \mu\text{F}$	-	3.0	-	A/ms

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Description

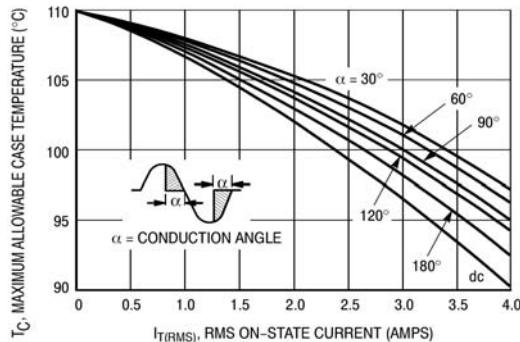


Figure 1. RMS Current Derating

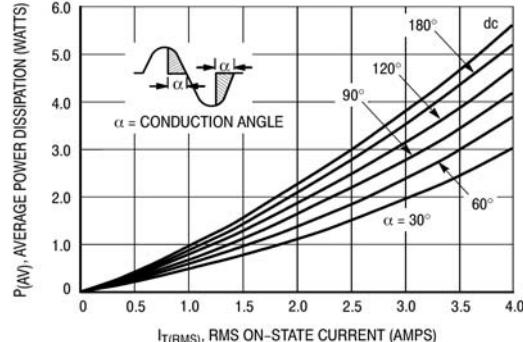


Figure 2. On-State Power Dissipation

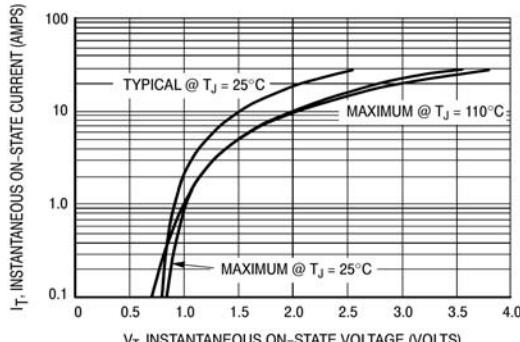


Figure 3. On-State Characteristics

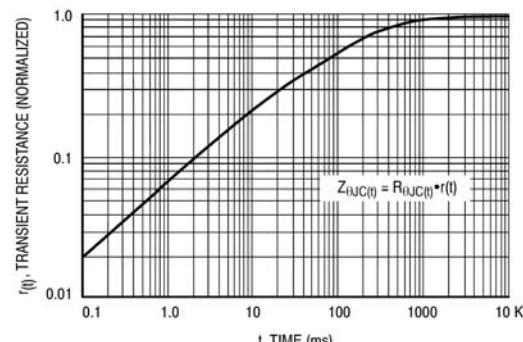


Figure 4. Transient Thermal Response

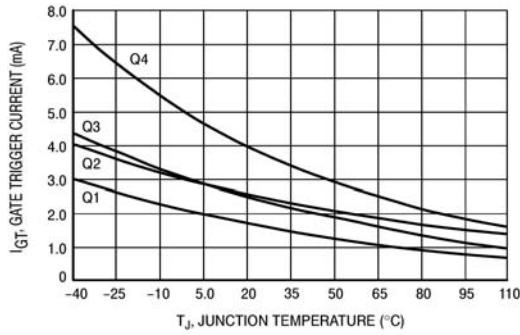


Figure 5. Typical Gate Trigger Current versus Junction Temperature

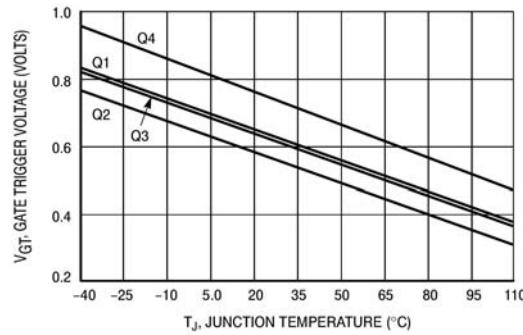


Figure 6. Typical Gate Trigger Voltage versus Junction Temperature

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Description

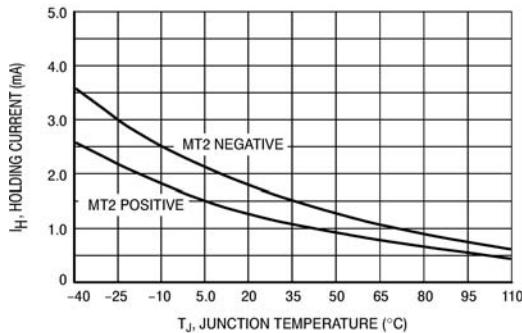


Figure 7. Typical Holding Current versus Junction Temperature

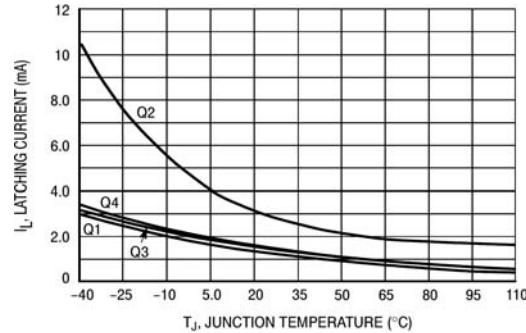


Figure 8. Typical Latching Current versus Junction Temperature

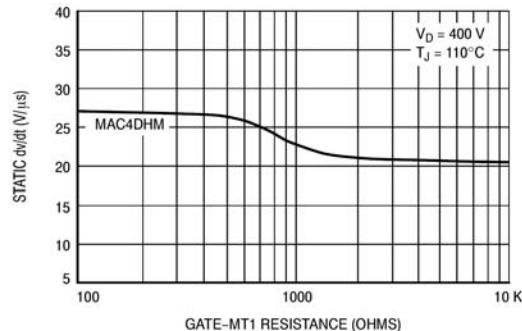


Figure 9. Minimum Exponential Static dv/dt versus Gate-MT1 Resistance

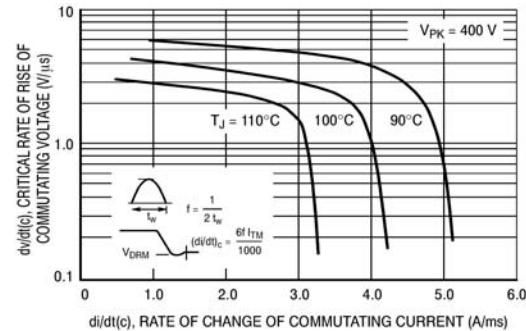
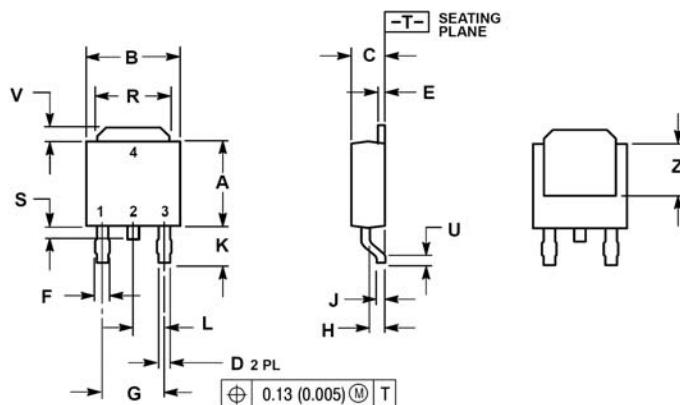


Figure 10. Typical Critical Rate of Rise of Commutating Voltage

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MECHANICAL DATA

Dimensions in mm
Net Mass: 0.45 g



NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.22
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.180	BSC	4.58	BSC
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.102	0.114	2.60	2.89
L	0.090	BSC	2.29	BSC
R	0.180	0.215	4.57	5.45
S	0.025	0.040	0.63	1.01
U	0.020	---	0.51	---
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

STYLE 6:
 PIN 1. MT1
 2. MT2
 3. GATE
 4. MT2